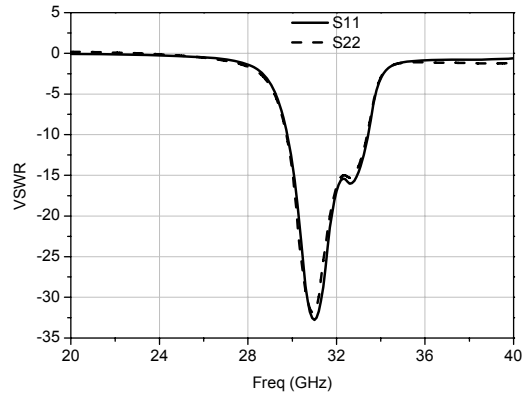


Features

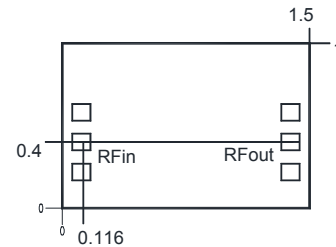
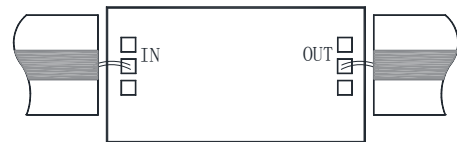
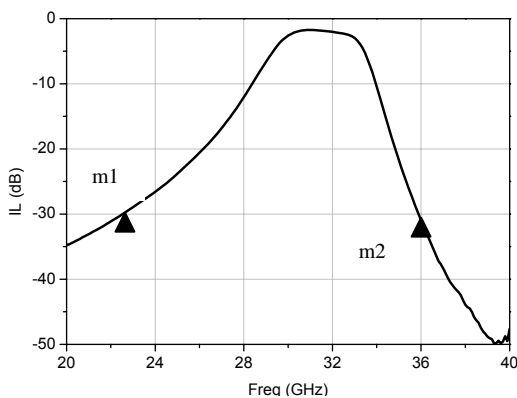
Pass Band: 30.5~32.5GHz
 Insertion Loss: 1.7 dB
 Stop Band Rejection: 30dB@22.6GHz,
 30.7dB@36GHz
 Return Loss: 15dB/15dB
 Chip Size: 1.5mm×1mm×0.1mm

General Description

The HG118L is a GaAs pHEMT band pass filter. Pass band Covers 30.5 to 32.5 GHz, this filter offers very low insertion loss of 1.7dB in pass band, and the return loss is 15dB.

Return Loss

Electrical Specifications(T_A=25 °C)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	30.5~32.5		
Input Return Loss	-	15	-
Output Return Loss	-	15	-
Pass Band Insertion Loss(dB)	-	-	1.7
Stop Band Rejection(dB)	-	30@22.6GHz	-
	-	30.7@36GHz	-

Outline Drawing (mm)

Assembly Diagram

Insertion Loss


m1
 Freq=22.6GHz
 dB(S(2,1)) = -30

m2
 Freq=36GHz
 dB(S(2,1)) = -30.7

Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with Φ25μm double gold wire bonding, suggested length of gold wire 250~400μm.
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.